





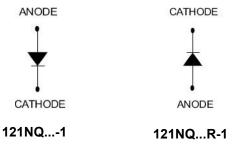
121NQ035/R-1 121NQ040/R-1 121NQ045/R-1 SCHOTTKY RECTIFIER



Features

- 175℃ T_J operation
- Unique high power, Half-Pak module
- Replaces three parallel DO-5'S
- Easier to mount and lower profile than DO-5'S
- High purity, high temperature epoxy encapsulation for enhanced
- mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Base plate: Nickel plated; Terminals: Nickel plated
- This is a Pb Free Device
- . All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

The top side is terminal, the bottom side is base plate.

Maximum Ratings (limiting values, at 25 °C unless otherwise specified)

Characteristics	Symbol	Condition	Max.		Units
Peak Repetitive Reverse Voltage	V_{RRM}	-	35	121NQ035(R)-1	
Working Peak Reverse Voltage	V_{RWM}		40 121NQ040(R)-1		V
DC Blocking Voltage	V_R		45	121NQ045(R)-1	
Average Forward Current	I _{F(AV)}	50% duty cycle @T _C =133°C, rectangular wave form	120		А
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse	2640		Α
Non-Repetitive Avalanche Energy	E _{AS}	T _J =25°C,I _{AS} =12A,L=1.12mH	81		mJ
Repetitive Avalanche Current	I _{AR}	Current decaying linearly to zero in 1 µsec Frequency limited by T_J max. $V_A=1.5\times V_R$ typical	12		Α

- China Germany Korea Singapore United States
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Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	\/_	@ 120A, Pulse, T _J = 25 °C	0.65	0.70	V
	V_{F1}	@ 240A, Pulse, T _J = 25 °C	0.81	0.83	V
	\/_	@ 120A, Pulse, T _J = 125 °C	0.60	0.65	V
	V_{F2}	@ 240A, Pulse, T _J = 125 °C	0.71	0.75	V
Reverse Current*	I _{R1}	@V _R = rated VR T _J = 25 °C	0.04	10	mA
	I _{R2}	@V _R = rated VR T _J = 125 °C	10	90	mA
Threshold Voltage	$V_{F(TO)}$	Tı = Tı max	-	0.32	V
Forward Slope Resistance	r _t	TJ = TJIIIAX	-	1.37	mΩ
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 ^{\circ}C$ $f_{SIG} = 1MHz$	4310	5200	pF
Max. Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

 $^{^{\}star}\,$ Pulse width < 300 $\mu s,\,$ duty cycle < 2%

Thermal-Mechanical Specifications:

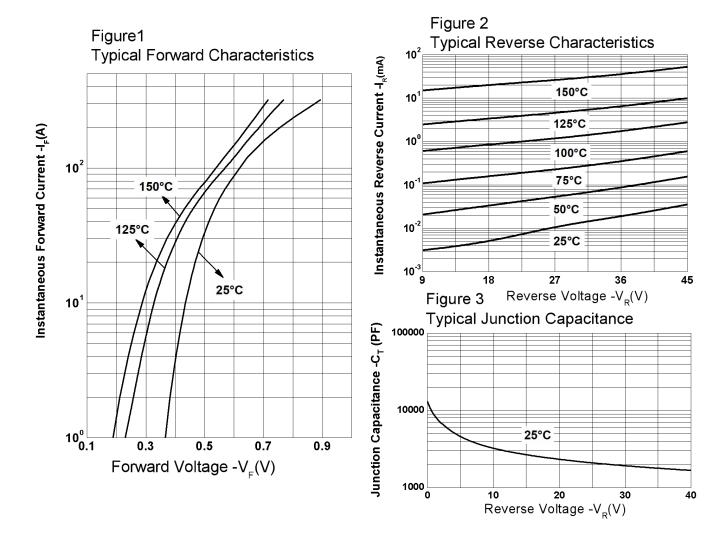
Characteristics	Symbol	Condition	Specific	Units	
Junction Temperature	TJ	-	-55 to +175		°C
Storage Temperature	T _{stg}	-	-55 to +175		°C
Typical Thermal Resistance Junction to Case	R _θ JC	DC operation	0.25		°C/W
Typical Thermal Resistance, case to Heat Sink	$R_{ heta cs}$	Mounting surface, smooth and greased	0.07		°C/W
Mounting Torque	Тм	Non-lubricated threads	Mounting Torque Terminal Torque	23(min) 29(max) 35(min) 46(max)	Kg-cm
Approximate Weight	wt	-	36		g
Case Style	PRM1-1				







Ratings and Characteristics Curves



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Ordering Information

Device	Package	Shipping	
121NQ SERIES	PRM1-1(Pb-Free)	27pcs/ box	

Marking Diagram

SS XXXX

121NQ035-1

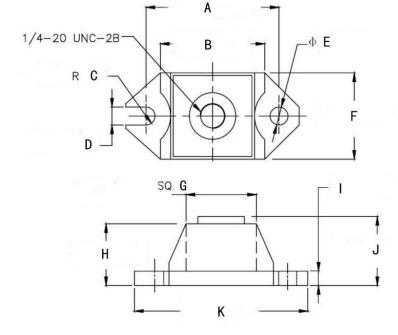
Where XXXX is YYWW

1st row SS YYWW 2nd row 121NQ035-1 SS = SS = Year WW = Week

Cautions: Molding resin

Epoxy resin UL:94V-0

Mechanical Dimensions PRM1-1 (Inches/Millimeters)



SYMBOL	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
Α	29.35	30.95	1.155	1.219	
В	24.77	26.04	0.975	1.026	
С	1.79	2.19	0.070	0.087	
D	3.73	4.24	0.146	0.167	
Е	3.73	4.24	0.146	0.167	
F	18.42	19.69	0.725	0.775	
G	18.55	19.55	0.730	0.770	
Н	13.59	14.47	0.535	70.500	
I	3.05	3.90	0.120	0.154	
J	14.87	15.87	0.585	0.625	
К	38.61	39.62	1.520	1.560	

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